



P-Channel 1.25-W, 1.8-V (G-S) MOSFET

CHARACTERISTICS

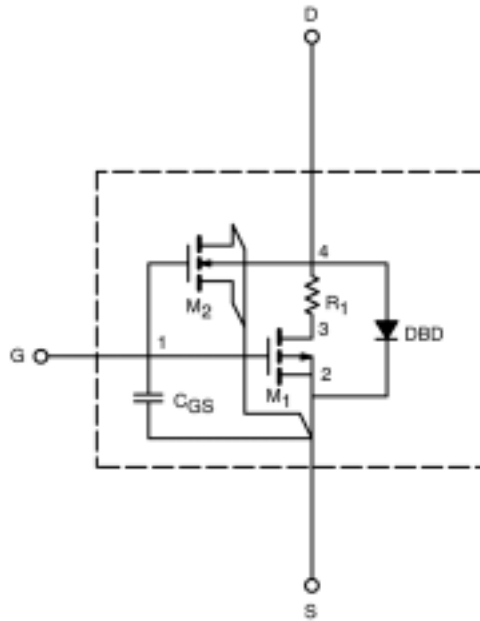
- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model schematic is extracted and optimized over the -55 to 125°C temperature ranges under the pulsed 0-to-5V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

SPICE Device Model Si2305DS

Vishay Siliconix



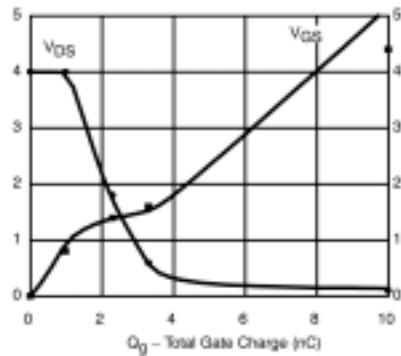
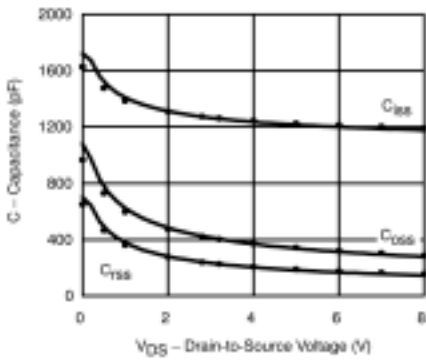
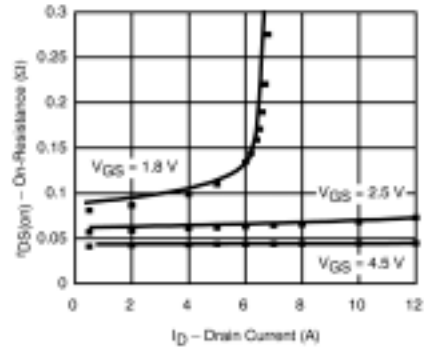
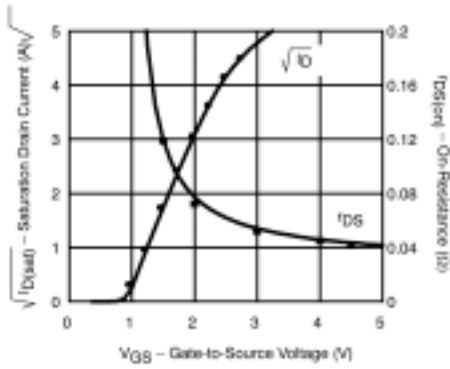
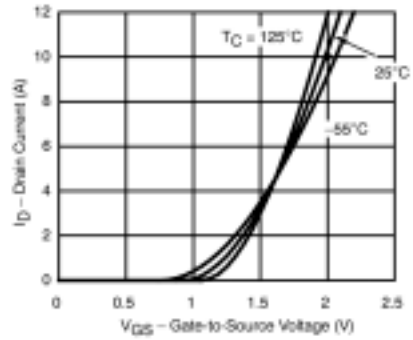
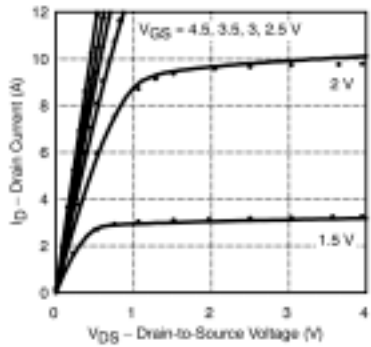
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	Test Conditions	Typical	Unit
Static				
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	0.78	V
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	77	A
		$V_{DS} \geq -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	20	
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -3.5 \text{ A}$	0.044	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -3.0 \text{ A}$	0.063	
		$V_{GS} = -1.8 \text{ V}, I_D = -2.0 \text{ A}$	0.095	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5 \text{ V}, I_D = -3.5 \text{ A}$	10	S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.6 \text{ A}, V_{GS} = 0 \text{ V}$	0.80	V
Dynamic^b				
Total Gate Charge	Q_g	$V_{DS} = -4 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -3.5 \text{ A}$	9	nC
Gate-Source Charge	Q_{gs}		2	
Gate-Drain Charge	Q_{gd}		1.5	
Input Capacitance	C_{iss}	$V_{GS} = -4 \text{ V}, V_{DS} = 0 \text{ V}, f = 1 \text{ MHz}$	1237	pf
Output Capacitance	C_{oss}		370	
Reverse Transfer Capacitance	C_{rss}		205	
Switching^c				
Turn-On Delay Time ^b	$t_{d(on)}$	$V_{DD} = -4 \text{ V}, R_L = 4 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_G = 6 \Omega$	31	ns
Rise Time	t_r		23	
Turn-Off Delay Time ^b	$t_{d(off)}$		54	
Fall Time	t_f		13	

Notes

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- b. For design aid only, not subject to production testing
- c. Switching time is essentially independent of operating temperature



COMPARISON OF MODEL WITH MEASURED DATA ($T_J=25^\circ\text{C}$ UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.